40V 175°C N-CHANNEL ENHANCEMENT MODE MOSFET
TO263AB

Product Summary

BV_{DSS}	$R_{DS(ON)}$ Max	I_D T_C = +25°C
40V	3mΩ @ V_{GS} = 10V	192A

Features

- Rated to +175°C—Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switching (UIS) Test in Production – Ensures More Reliable and Robust End Application
- Low $R_{DS(ON)}$—Minimizes Power Losses
- Low Q_g—Minimizes Switching Losses
- **Lead-Free Finish; RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **The DMTH4002SCTBQ is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF 16949 certified facilities.**
  https://www.diodes.com/quality/product-definitions/

Description and Applications

This MOSFET is designed to meet the stringent requirements of automotive applications. It is qualified to AEC-Q101, supported by a PPAP, and is ideal for use in:

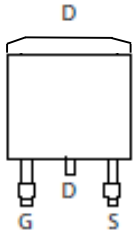
- Engine Management Systems
- Body Control Electronics
- DC-DC Converters

Mechanical Data

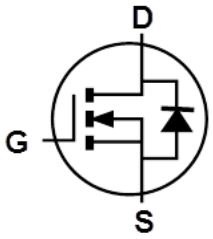
- Case: TO263AB
- Case Material: Molded Plastic, "Green" Molding Compound; UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Finish — Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 e3
- Weight: 1.7 grams (Approximate)

TO263AB (D2PAK)

Top View



Pin Out Top View



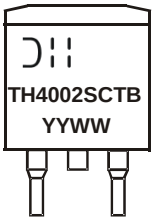
Internal Schematic

Ordering Information (Note 4)

Part Number	Case	Packaging
DMTH4002SCTBQ-13	TO263AB (D2PAK)	800/Tape & Reel

Notes:
1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2), & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



TH4002SCTB = Product Type Marking Code
YYWW = Date Code Marking
YY = Last Two Digits of Year (ex: 20 = 2020)
WW = Week (01 to 53)

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Drain-Source Voltage		V_{DSS}	40	V
Gate-Source Voltage		V_{GSS}	±20	V
Continuous Drain Current (Note 6)	T_C = +25°C	I_D	192	A
	T_C = +100°C		136	
Maximum Continuous Body Diode Forward Current (Note 6)	T_C = +25°C	I_S	100	A
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)		I_{DM}	760	A
Pulsed Body Diode Forward Current (10µs Pulse, Duty Cycle = 1%)		I_{SM}	760	A
Avalanche Current, L = 3mH		I_{AS}	19.2	A
Avalanche Energy, L = 3mH		E_{AS}	551.8	mJ

Thermal Characteristics

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	T_A = +25°C	P_D	6	W
Thermal Resistance, Junction to Ambient (Note 5)		$R_{\Theta JA}$	25	°C/W
Total Power Dissipation (Note 6)	T_C = +25°C	P_D	166.7	W
Thermal Resistance, Junction to Case (Note 6)		$R_{\Theta JC}$	0.9	°C/W
Operating and Storage Temperature Range		T_J, T_{STG}	-55 to +175	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV_{DSS}	40	—	—	V	V_{GS} = 0V, I_D = 1mA
Zero Gate Voltage Drain Current	I_{DSS}	—	—	1	µA	V_{DS} = 32V, V_{GS} = 0V
Gate-Source Leakage	I_{GSS}	—	—	±100	nA	V_{GS} = ±20V, V_{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	$V_{GS(TH)}$	2	—	4	V	V_{DS} = V_{GS}, I_D = 250µA
Static Drain-Source On-Resistance	$R_{DS(ON)}$	—	2.22	3	mΩ	V_{GS} = 10V, I_D = 90A
Diode Forward Voltage	V_{SD}	—	0.8	1.2	V	V_{GS} = 0V, I_S = 20A
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C_{iss}	—	7180	—	pF	V_{DS} = 20V, V_{GS} = 0V, f = 1MHz
Output Capacitance	C_{oss}	—	1698	—		
Reverse Transfer Capacitance	C_{rss}	—	17	—		
Gate Resistance	R_G	—	1.04	—	Ω	V_{DS} = 0V, V_{GS} = 0V, f = 1MHz
Total Gate Charge	Q_g	—	77.5	—	nC	V_{DD} = 20V, I_D = 90A, V_{GS} = 10V
Gate-Source Charge	Q_{gs}	—	23.6	—		
Gate-Drain Charge	Q_{gd}	—	13.6	—		
Turn-On Delay Time	$t_{D(ON)}$	—	16.8	—	ns	V_{DD} = 20V, V_{GS} = 10V, I_D = 90A, R_G = 3.5Ω
Turn-On Rise Time	t_R	—	8.0	—		
Turn-Off Delay Time	$t_{D(OFF)}$	—	35.8	—		
Turn-Off Fall Time	t_F	—	11.6	—		
Reverse Recovery Time	t_{RR}	—	46.36	—	ns	I_F = 15A, di/dt = 100A/µs
Reverse Recovery Charge	Q_{RR}	—	56.11	—	nC	

Notes: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1-inch square copper plate.
6. Thermal resistance from junction to soldering point (on the exposed drain pad).
7. Short duration pulse test used to minimize self-heating effect.
8. Guaranteed by design. Not subject to product testing.

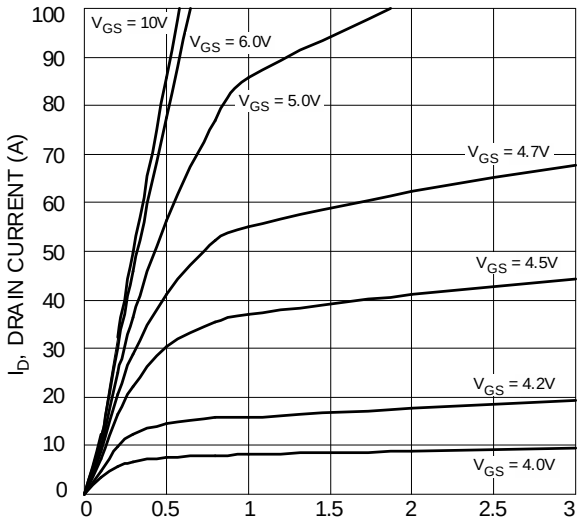


Figure 1 Typical Output Characteristic

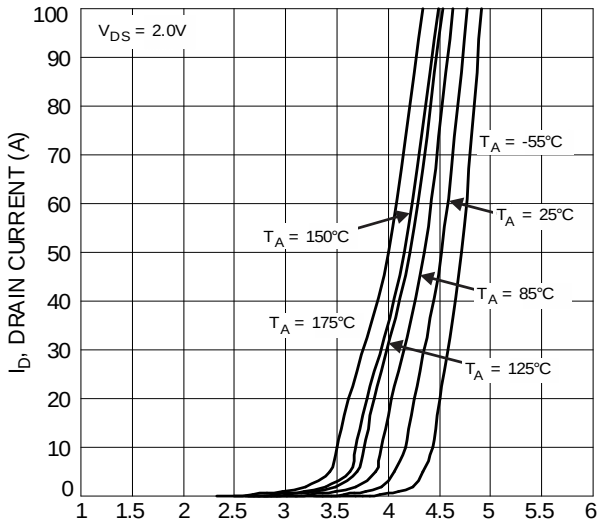


Figure 2 Typical Transfer Characteristics

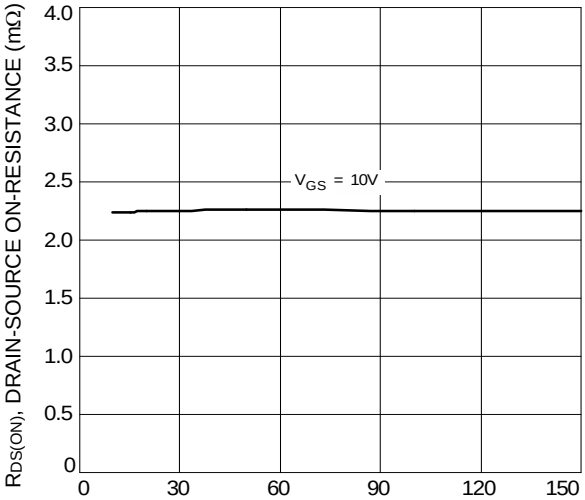


Figure 3 Typical On-Resistance vs. Drain Current and Gate Voltage

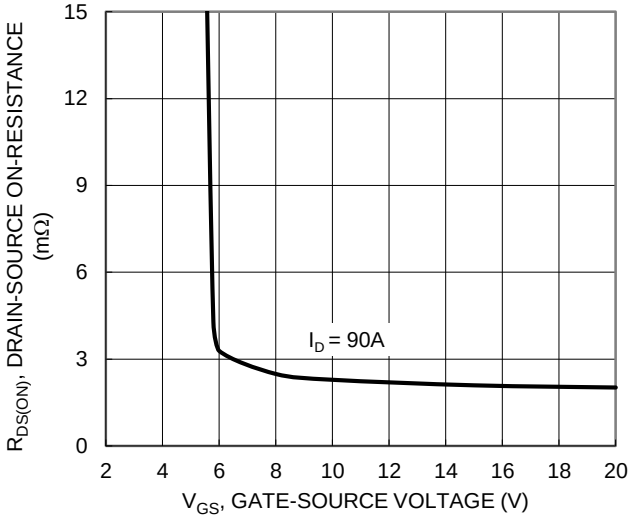


Figure 4. Typical Transfer Characteristic

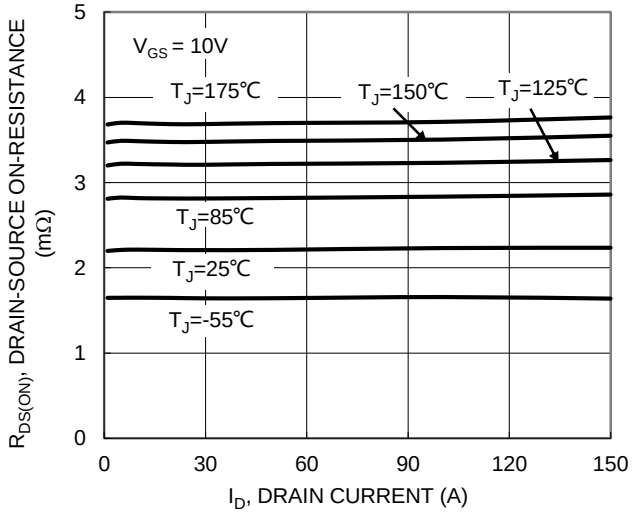


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

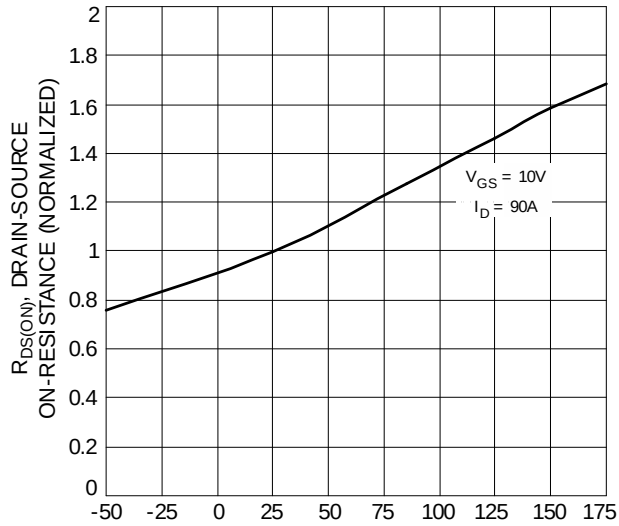


Figure 6 On-Resistance Variation with Temperature

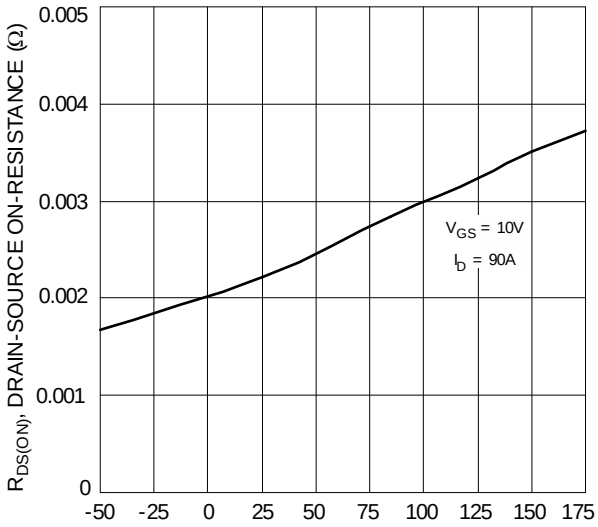


Figure 7 On-Resistance Variation with Temperature

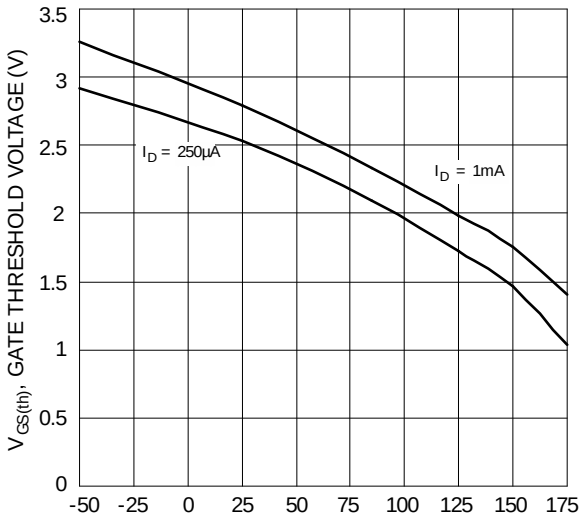


Figure 8 Gate Threshold Variation vs. Junction Temperature

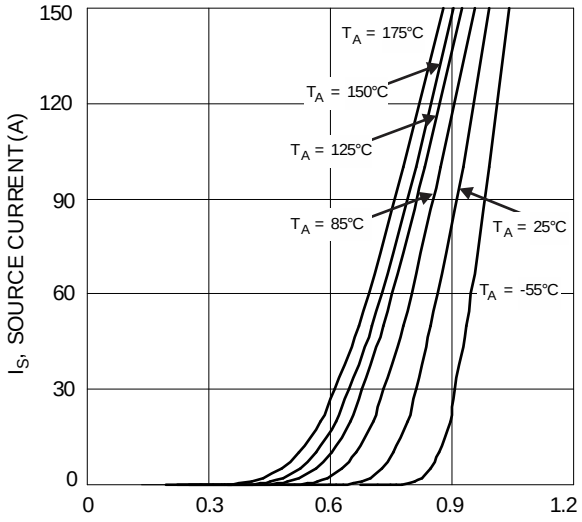


Figure 9 Diode Forward Voltage vs. Current

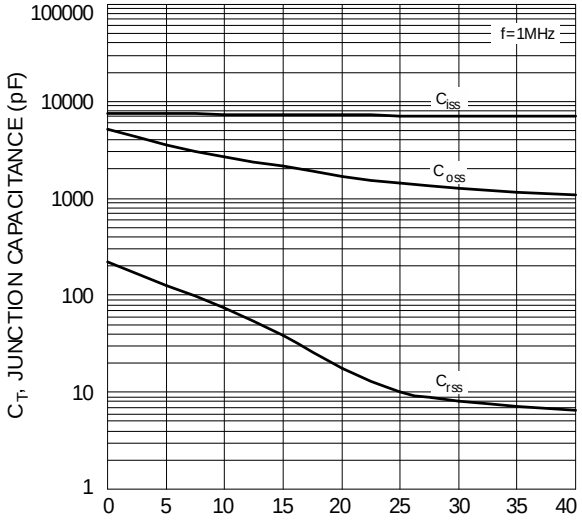


Figure 10 Typical Junction Capacitance

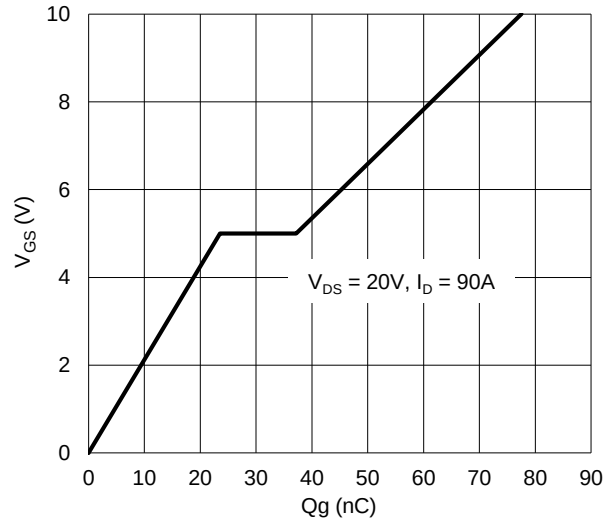


Figure 11. Gate Charge

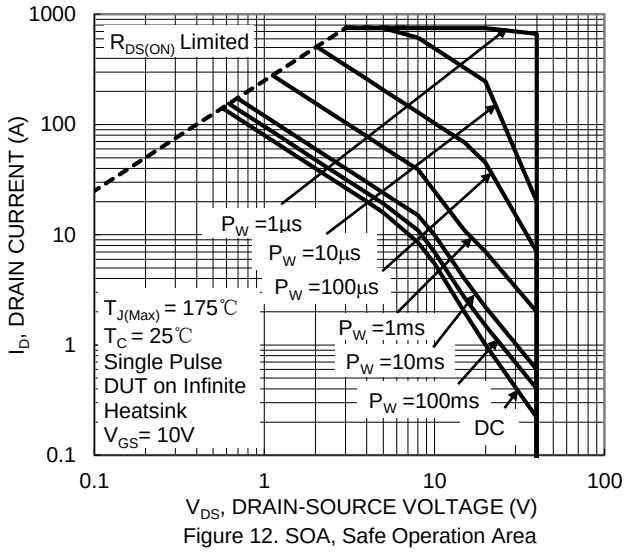


Figure 12. SOA, Safe Operation Area

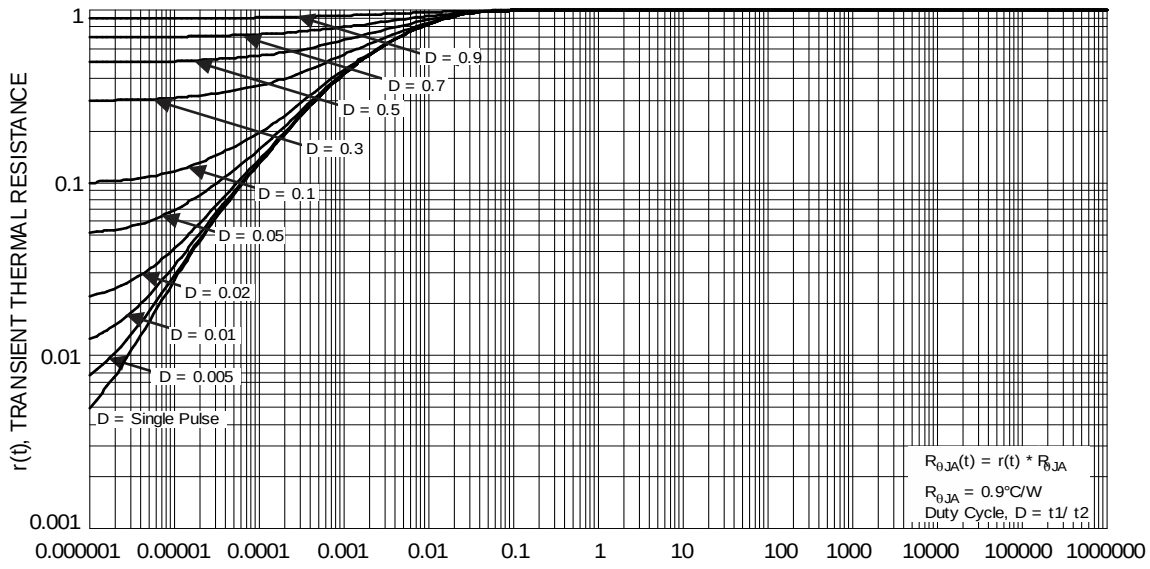
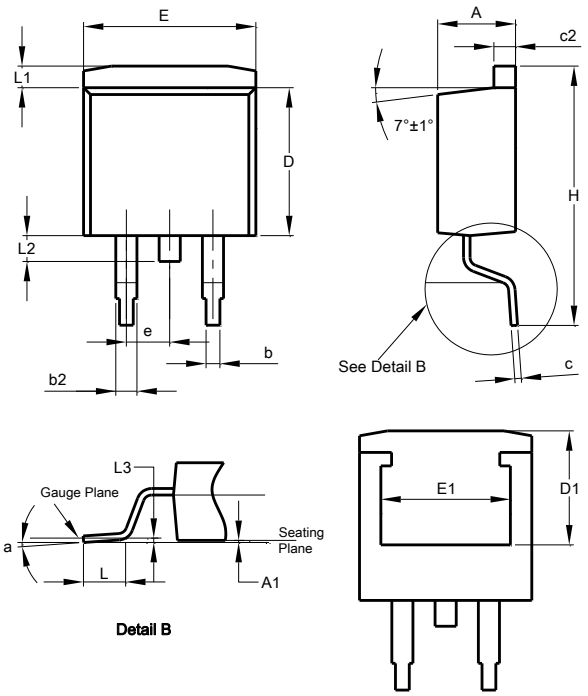


Figure 13 Transient Thermal Resistance

Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

TO263AB (D2PAK)

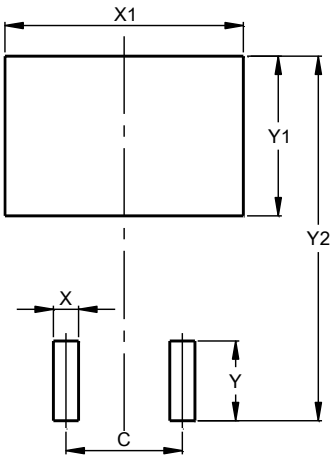


TO263AB (D2PAK)			
Dim	**Min**	**Max**	**Typ**
A	4.07	4.82	—
A1	0.00	0.25	—
b	0.51	0.99	—
b2	1.15	1.77	—
c	0.356	0.73	—
c2	1.143	1.65	—
D	8.39	9.65	—
D1	6.55	6.95	—
e	2.54 TYP		
E	9.66	10.66	—
E1	6.23	8.23	—
H	14.61	15.87	—
L	1.78	2.79	—
L1	—	1.67	—
L2	—	1.77	—
L3	—	—	0.254
a	0°	8°	—
All Dimensions in mm			

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

TO263AB (D2PAK)



Dimensions	Value (in mm)
C	5.08
X	1.10
X1	10.41
Y	3.50
Y1	7.01
Y2	15.99

IMPORTANT NOTICE

DIODES INCORPORATED MAKES NO WARRANTY OF ANY KIND, EXPRESS OR IMPLIED, WITH REGARDS TO THIS DOCUMENT, INCLUDING, BUT NOT LIMITED TO, THE IMPLIED WARRANTIES OF MERCHANTABILITY AND FITNESS FOR A PARTICULAR PURPOSE (AND THEIR EQUIVALENTS UNDER THE LAWS OF ANY JURISDICTION).

Diodes Incorporated and its subsidiaries reserve the right to make modifications, enhancements, improvements, corrections or other changes without further notice to this document and any product described herein. Diodes Incorporated does not assume any liability arising out of the application or use of this document or any product described herein; neither does Diodes Incorporated convey any license under its patent or trademark rights, nor the rights of others. Any Customer or user of this document or products described herein in such applications shall assume all risks of such use and will agree to hold Diodes Incorporated and all the companies whose products are represented on Diodes Incorporated website, harmless against all damages.

Diodes Incorporated does not warrant or accept any liability whatsoever in respect of any products purchased through unauthorized sales channel. Should Customers purchase or use Diodes Incorporated products for any unintended or unauthorized application, Customers shall indemnify and hold Diodes Incorporated and its representatives harmless against all claims, damages, expenses, and attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized application.

Products described herein may be covered by one or more United States, international or foreign patents pending. Product names and markings noted herein may also be covered by one or more United States, international or foreign trademarks.

This document is written in English but may be translated into multiple languages for reference. Only the English version of this document is the final and determinative format released by Diodes Incorporated.

LIFE SUPPORT

Diodes Incorporated products are specifically not authorized for use as critical components in life support devices or systems without the express written approval of the Chief Executive Officer of Diodes Incorporated. As used herein:

A. Life support devices or systems are devices or systems which:

1. are intended to implant into the body, or

2. support or sustain life and whose failure to perform when properly used in accordance with instructions for use provided in the labeling can be reasonably expected to result in significant injury to the user.

B. A critical component is any component in a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or to affect its safety or effectiveness.

Customers represent that they have all necessary expertise in the safety and regulatory ramifications of their life support devices or systems, and acknowledge and agree that they are solely responsible for all legal, regulatory and safety-related requirements concerning their products and any use of Diodes Incorporated products in such safety-critical, life support devices or systems, notwithstanding any devices- or systems-related information or support that may be provided by Diodes Incorporated. Further, Customers must fully indemnify Diodes Incorporated and its representatives against any damages arising out of the use of Diodes Incorporated products in such safety-critical, life support devices or systems.

www.diodes.com